

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (U-MOSII)

# TPC8006-H

LITHIUM ION BATTERY APPLICATIONS

NOTE BOOK PC, PORTABLE EQUIPMENTS APPLICATIONS

HIGH SPEED AND HIGH EFFICIENCY DC-DC CONVERTERS

INDUSTRIAL APPLICATIONS

Unit in mm

- High Speed Switching : 60% speed up  
(compare with current type)
- Small Gate Charge :  $Q_g = 16 \text{ nC}$  (Typ.)
- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 19 \text{ m}\Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 8.8 \text{ S}$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 10 \mu\text{A}$  (Max.) ( $V_{DS} = 30 \text{ V}$ )
- Enhancement-Mode :  $V_{th} = 1.3 \sim 2.5 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	30	V
Drain-Gate Voltage ( $R_{GS} = 20\text{k}\Omega$ )	$V_{DGR}$	30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	DC	$I_D$	7 A
	Pulse	$I_{DP}$	28 A
Drain Power Dissipation*** ( $T_a = 25^\circ\text{C}$ )	$P_D$	2.4	W
Single Pulse Avalanche Energy**	$E_{AS}$	63.7	mJ
Avalanche Current	$I_{AR}$	7	A
Repetitive Avalanche Energy*	$E_{AR}$	0.24	mJ
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	$-55 \sim 150$	$^\circ\text{C}$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient***	$R_{th(ch-a)}$	52.1	$^\circ\text{C}/\text{W}$

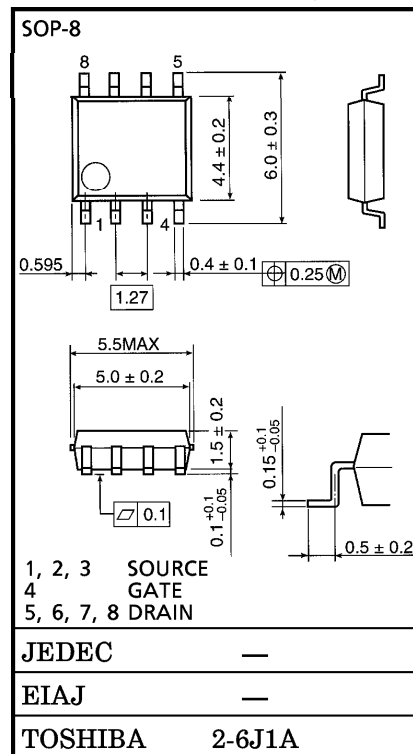
Note ;

\* Repetitive rating ; Pulse Width Limited by Max. Junction Temperature.

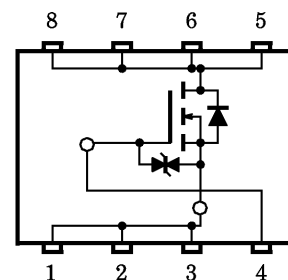
\*\*  $V_{DD} = 24 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 1.0 \text{ mH}$ ,  $R_G = 25 \Omega$ ,  $I_{AR} = 7 \text{ A}$

\*\*\* Drive operation ; Mount on glass epoxy board [ $1 \text{ inch}^2 \times 0.8 \text{ t}$ ] ( $t = 10 \text{ s}$ )

**This transistor is an electrostatic sensitive device. Please handle with caution.**



CIRCUIT CONFIGURATION



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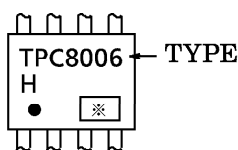
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V	—	—	±10	μA	
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	—	—	10	μA	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30	—	—	V	
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	15	—	—		
Gate Threshold Voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.3	—	2.5	V	
Drain-Source ON Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.5 A	—	29	40	mΩ	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.5 A	—	19	27		
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.5 A	4.4	8.8	—	S	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	—	790	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		—	110	—		
Output Capacitance	C <sub>oss</sub>		—	290	—		
Switching Time	Rise Time	t <sub>r</sub>		—	5	—	ns
	Turn-On Time	t <sub>on</sub>		—	13	—	
	Fall Time	t <sub>f</sub>		—	8	—	
	Turn-Off Time	t <sub>off</sub>		V <sub>IN</sub> : t <sub>r</sub> , t <sub>f</sub> < 5 ns Duty ≤ 1%, t <sub>w</sub> = 10 μs	—	36	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q <sub>g</sub>	V <sub>DD</sub> ≐ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7 A	—	16	—	nC	
Gate-Source Charge	Q <sub>gs</sub>		—	12	—		
Gate-Drain ("Miller") Charge	Q <sub>gd</sub>		—	4	—		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I <sub>DR</sub>	—	—	—	7	A
Pulse Drain Reverse Current	I <sub>DRP</sub>	—	—	—	28	A
Diode Forward Voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V	—	—	-1.2	V

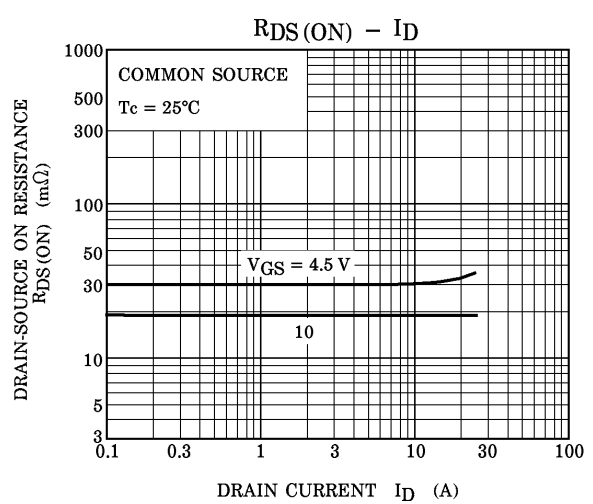
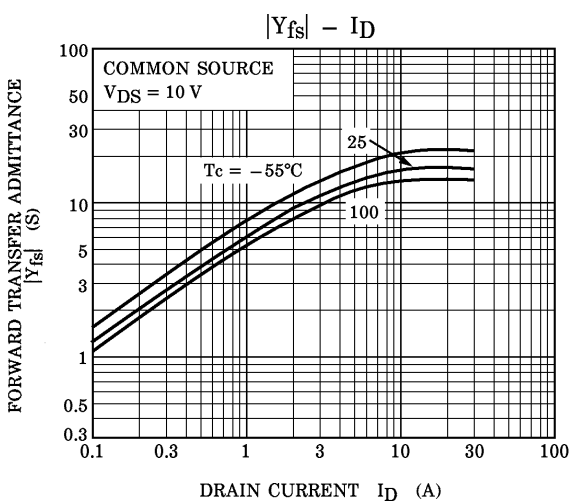
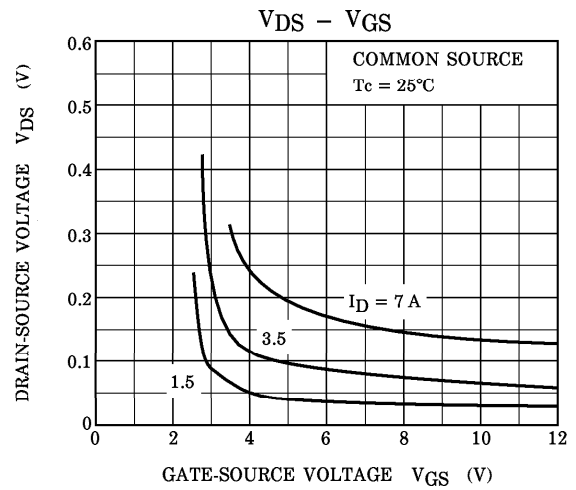
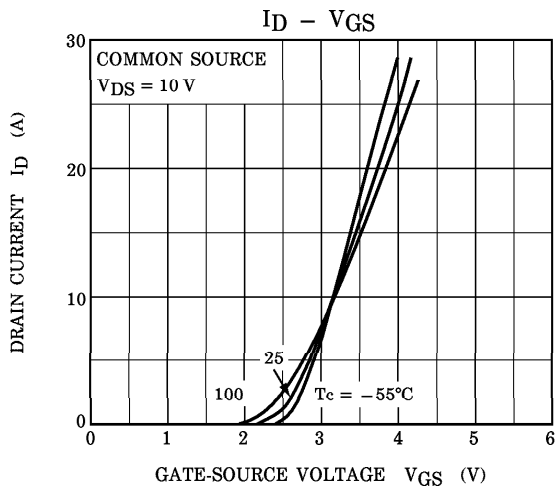
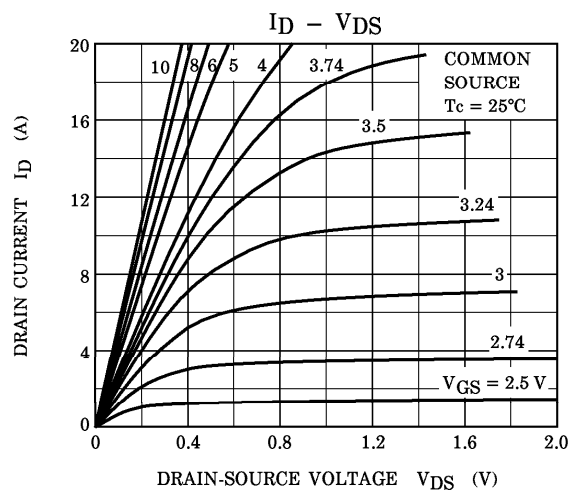
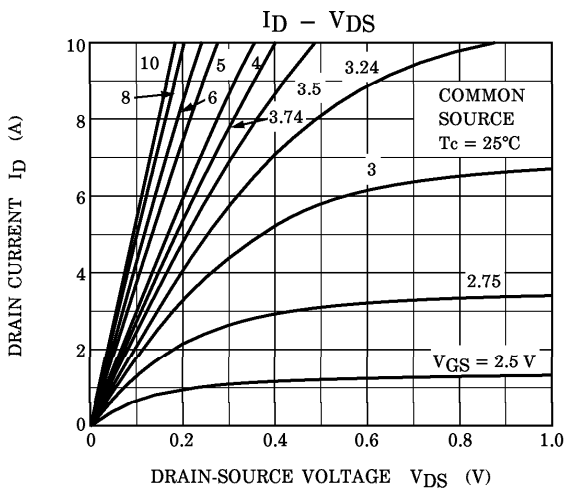
MARKING

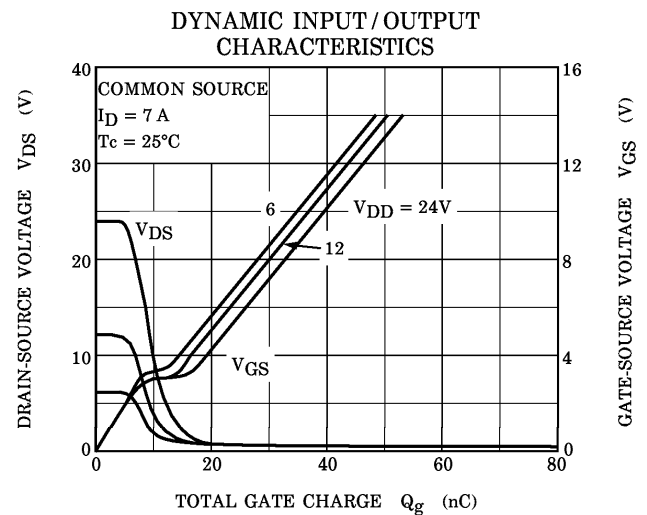
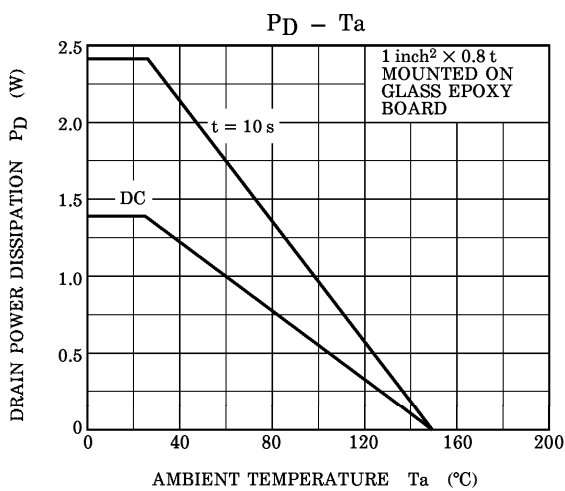
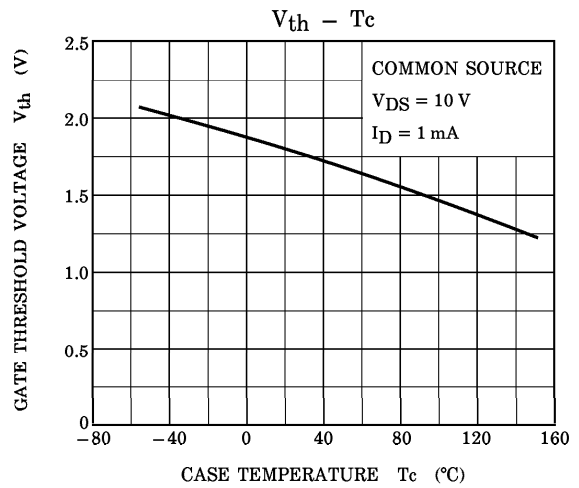
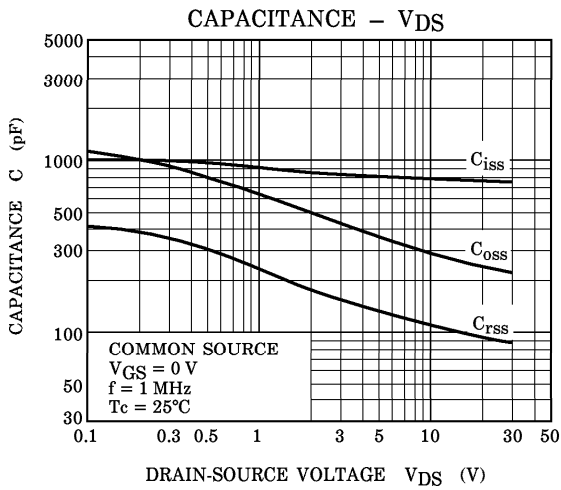
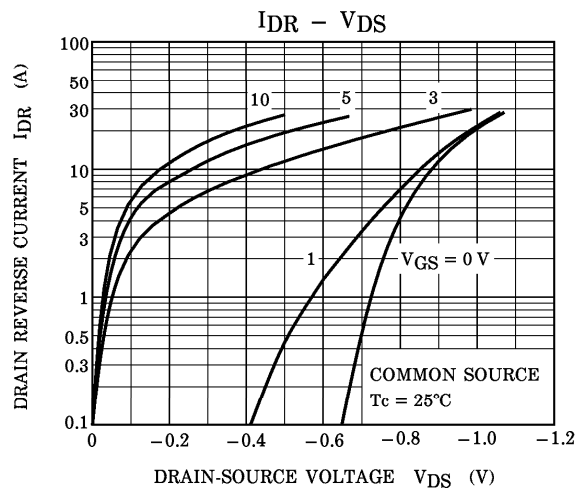
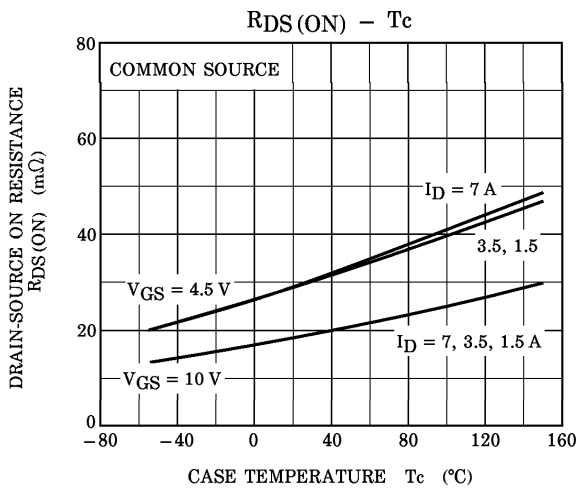


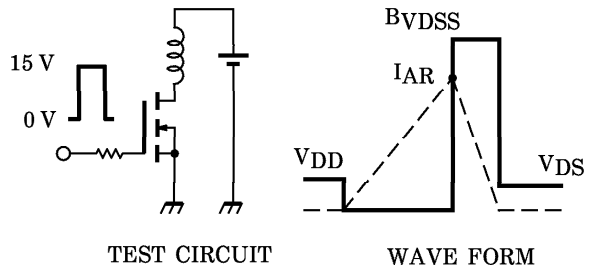
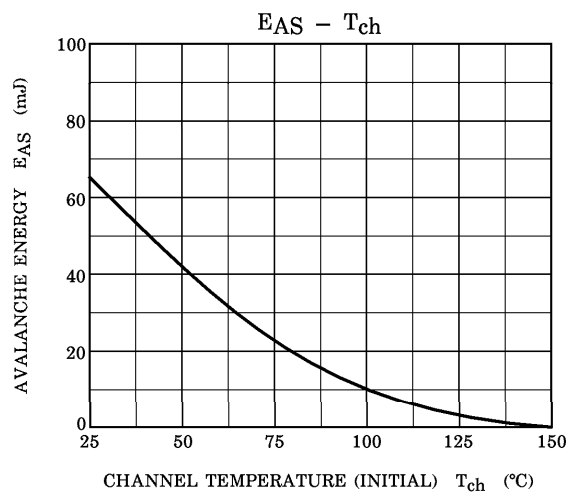
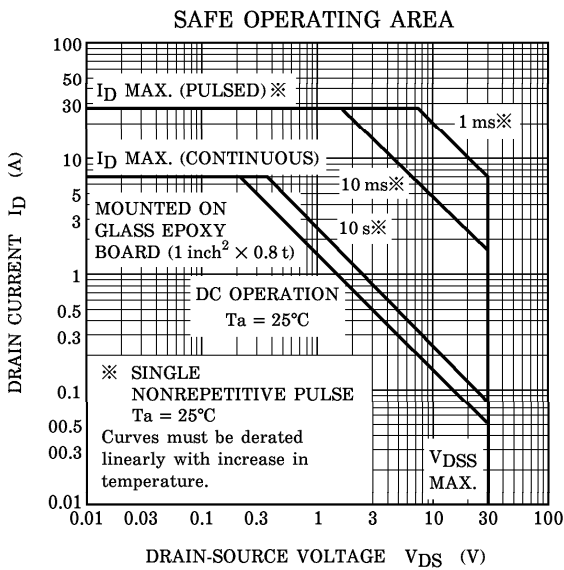
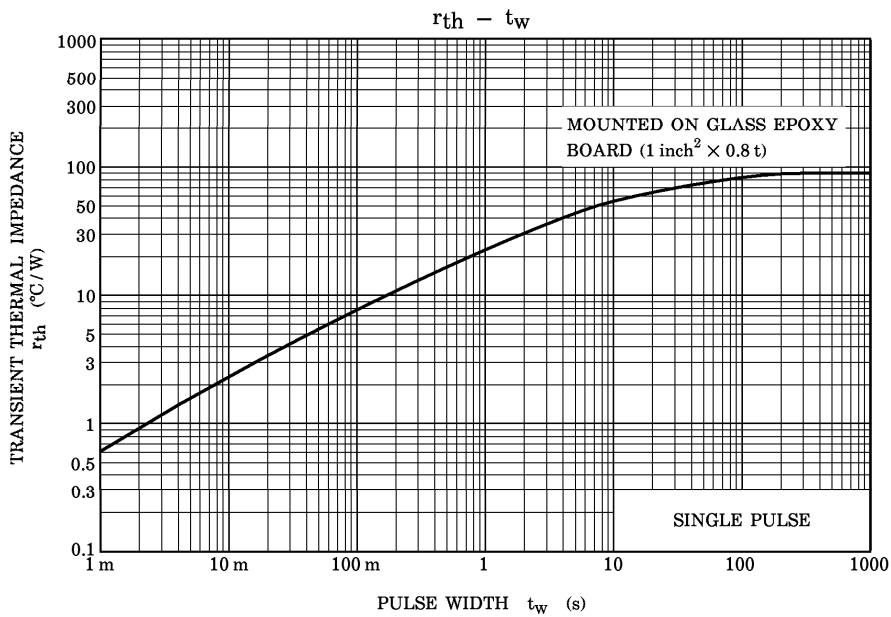
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak  $I_{AR} = 7 \text{ A}$ ,  $R_G = 25 \Omega$   
 $V_{DD} = 24 \text{ V}$ ,  $L = 1.0 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{V_{DS}}}{B_{V_{DS}} - V_{DD}} \right)$$